

High Voltage Standard Rectifier Module

$$\begin{aligned} V_{RRM} &= 2200 \text{ V} \\ I_{FAV} &= 560 \text{ A} \\ V_F &= 0.98 \text{ V} \end{aligned}$$

Single Diode

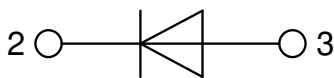
Part number

MDO500-22N1



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: Y1

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

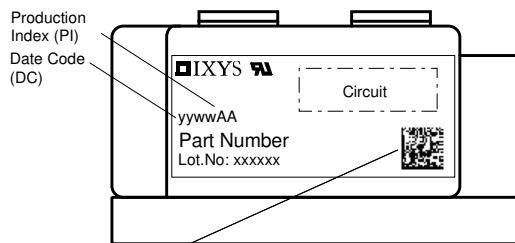
- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				2300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				2200	V
I_R	reverse current	$V_R = 2200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1	mA
		$V_R = 2200\text{ V}$	$T_{VJ} = 140^{\circ}\text{C}$			30	mA
V_F	forward voltage drop	$I_F = 500\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.09	V
		$I_F = 1000\text{ A}$				1.24	V
		$I_F = 500\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			0.98	V
		$I_F = 1000\text{ A}$				1.17	V
I_{FAV}	average forward current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 140^{\circ}\text{C}$			560	A
$I_{F(RMS)}$	RMS forward current	180° sine d = 0.5					A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 140^{\circ}\text{C}$		0.80	V
r_F	slope resistance					0.38	mΩ
R_{thJC}	thermal resistance junction to case					0.072	K/W
R_{thCH}	thermal resistance case to heatsink				0.024		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				1600	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			15.0	kA
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			16.2	kA
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140^{\circ}\text{C}$			12.8	kA
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			13.8	kA
I^2t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			1.13	MA ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			1.09	MA ² s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140^{\circ}\text{C}$			812.8	kA ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			788.8	kA ² s
C_J	junction capacitance	$V_R = 700\text{ V}; f = 1\text{ MHz}$			576		pF

Package Y1				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				600	A
T _{VJ}	virtual junction temperature			-40		140	°C
T _{op}	operation temperature			-40		125	°C
T _{stg}	storage temperature			-40		125	°C
Weight					650		g
M _D	mounting torque			4.5		7	Nm
M _T	terminal torque			11		13	Nm
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal		16.0			mm
d _{Spb/Apb}		terminal to backside		25.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	3600			V
		t = 1 minute		3000			V



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDO500-22N1	MDO500-22N1	Box	2	467219

Similar Part	Package	Voltage class
MDO500-12N1	Y1-2-CU	1200
MDO500-14N1	Y1-2-CU	1400
MDO500-16N1	Y1-2-CU	1600
MDO500-18N1	Y1-2-CU	1800
MDO500-20N1	Y1-2-CU	2000

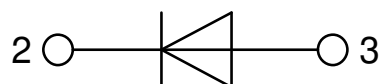
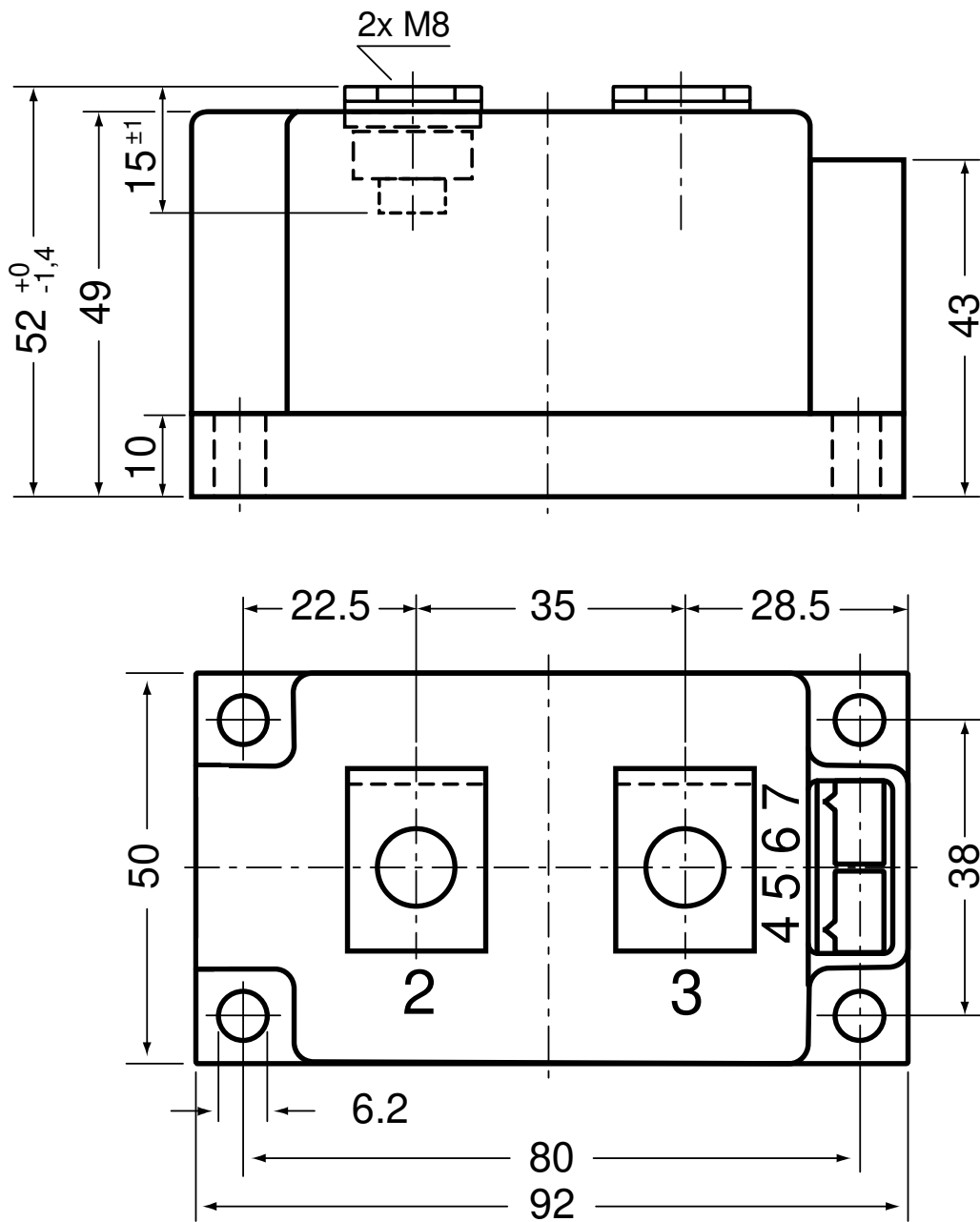
Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 140^\circ\text{C}$

			Rectifier
$V_{0\max}$	threshold voltage	0.8	V
$R_{0\max}$	slope resistance *	0.19	mΩ

Outlines Y1



Rectifier

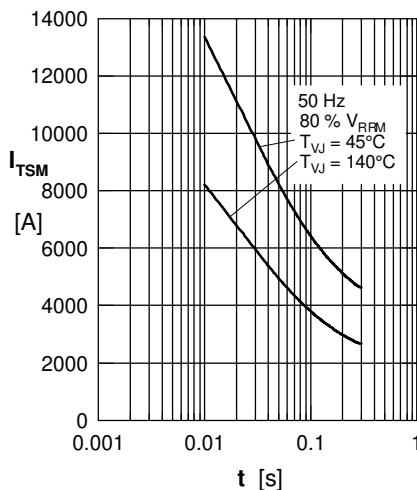


Fig. 1 Surge overload current
 I_{FSM} : Crest value, t : duration

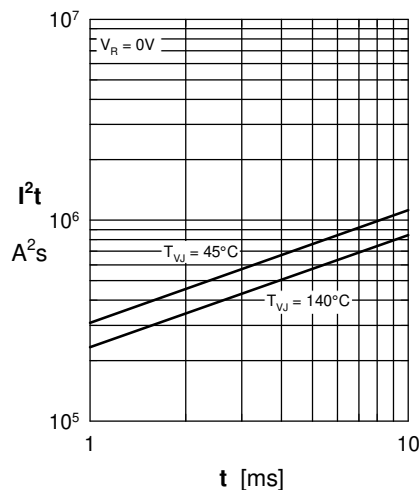


Fig. 2 I^2t versus time (1-10 ms)

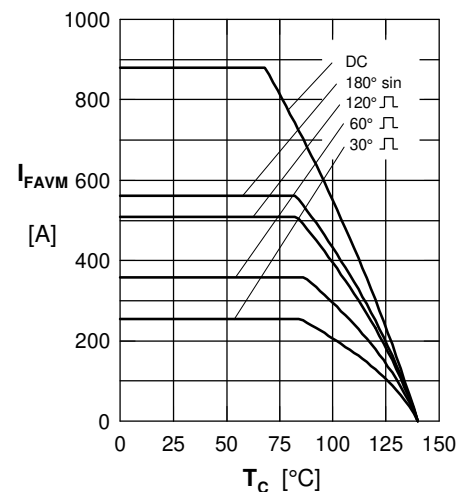


Fig. 3 Maximum forward current at case temperature

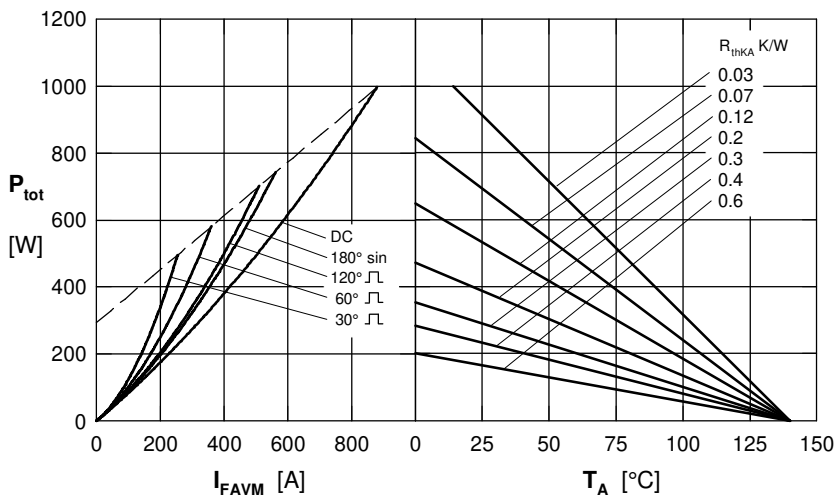


Fig. 4 Power dissipation vs. forward current and ambient temperature

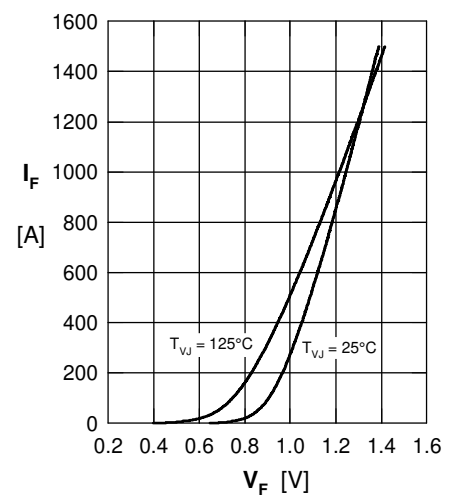


Fig. 5 Forward current I_F versus V_F

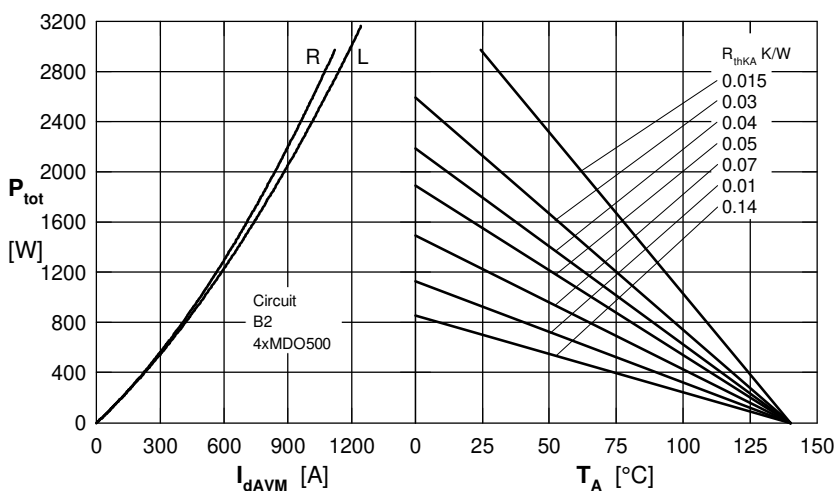


Fig. 6 Single phase rectifier bridge: Power dissipation vs. direct output current and ambient temperature. R = resistive load, L = inductive load

Rectifier

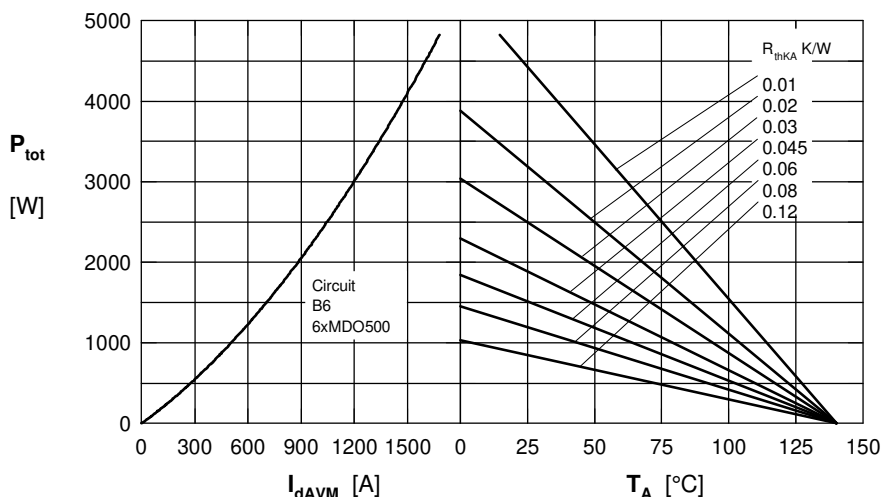


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

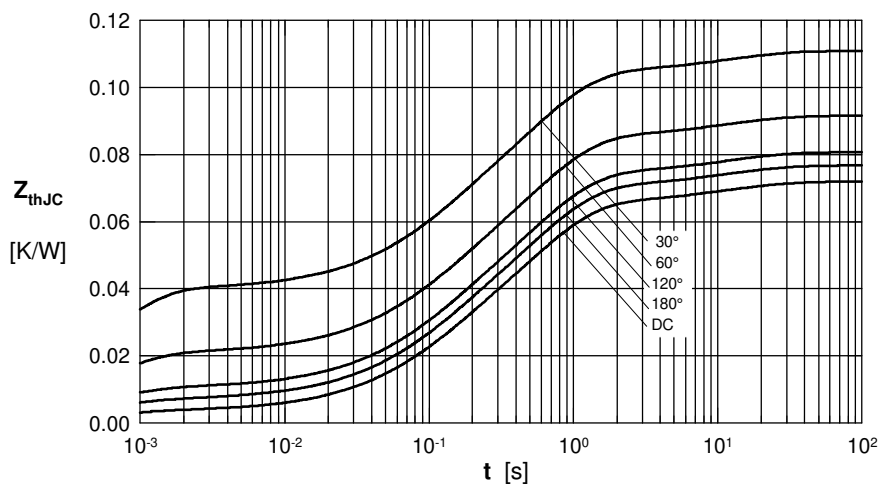


Fig. 7 Transient thermal impedance junction to case

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.072
180°	0.0768
120°	0.081
60°	0.092
30°	0.111

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0035	0.0054
2	0.0186	0.098
3	0.0432	0.54
4	0.0067	12

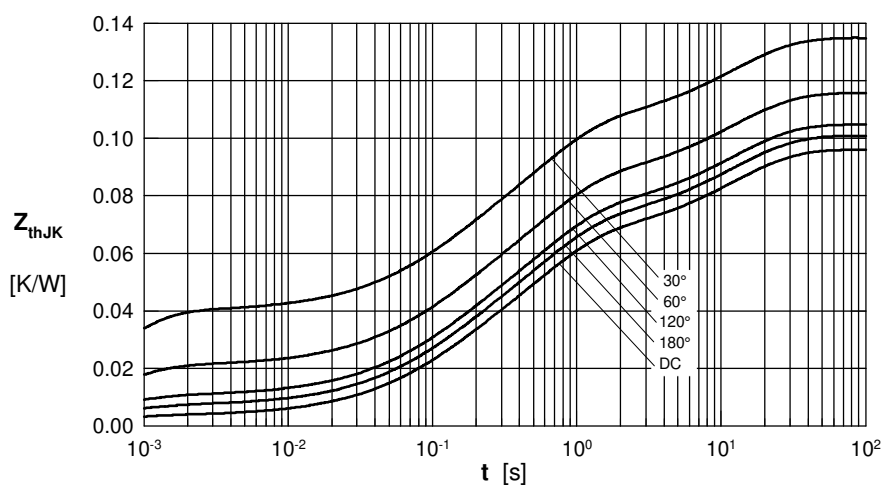


Fig. 8 Transient thermal impedance junction to heatsink

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.096
180°	0.1
120°	0.105
60°	0.116
30°	0.135

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0035	0.0054
2	0.0186	0.098
3	0.0432	0.54
4	0.0067	12
5	0.024	12